



**JMT110KH18T1**

## **Features**

- Half-bridge SCR configuration integrated in a single package
- High-thermal-conductctngl

## **Product Summary**



## Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
	$I_T=330\text{A}$ , $t_P=380\mu\text{s}$	$V_T$			1.80	V

$$V_D = V_{\text{DRM},T}$$

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## Ordering Information

Device	Marking	Package	Weight	Inner Box	Pre Carton
JMT110KH18T1	JMT110KH18T1	T1	100g 5/PCS	10 PCS	120 PCS

## Typical Electrical & Thermal Characteristics

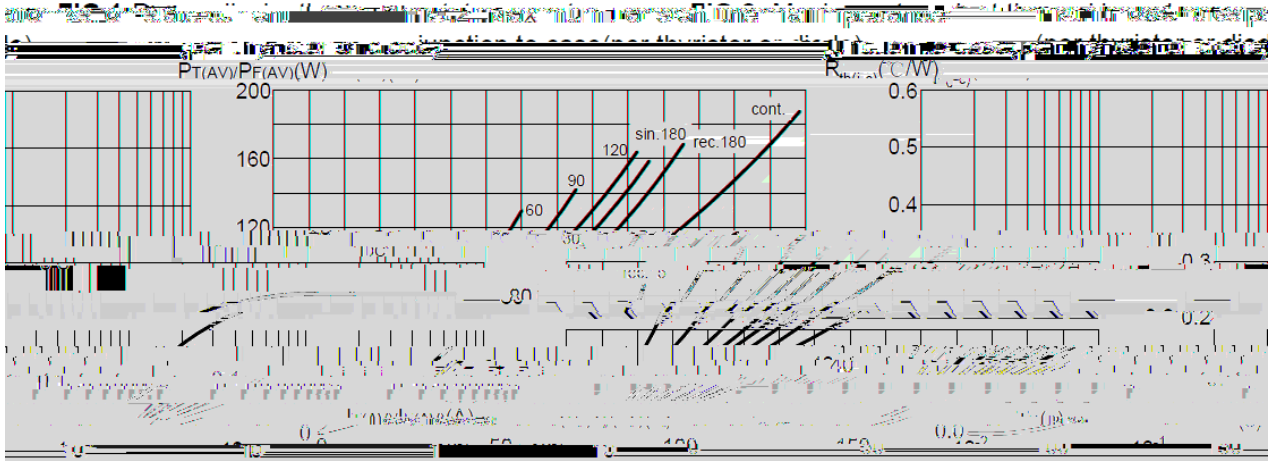


FIG 3: Forward characteristics

FIG 4: Relative variations of gate trigger current holding



